series resonance circuit with a reactance component of a gate-to-source impedance when a drain voltage of said FET is lower than a source voltage thereof;

wherein when a drain voltage of said FET is lower than a source voltage thereof, a series resonance circuit is formed of the reactance component of the gate-to-source impedance and said inductor element, and the inductance value of said inductor element is set in accordance with said predetermined frequency of said controlled signal.

11. (Twice Amended) A semiconductor integrated circuit comprising:

an FET having a gate terminal configured to input a controlled signal with a predetermined frequency and a drain terminal configured to output a signal corresponding to said controlled signal; and

an inductor element and a first capacitor element which are connected to each other in series between a source terminal of said FET and a ground terminal, said inductor element having an inductance value selected in accordance with the predetermined frequency of said controlled signal and forming a series resonance circuit with a reactance component of a gate-to-source impedance when a drain voltage of said FET is lower than a source voltage thereof;

wherein when a drain voltage of said FET is lower than a source voltage thereof, the series resonance circuit is formed of the reactance component of the gate-to-source impedance and said inductor element, and the inductance value of said inductor element is set in accordance with the predetermined frequency of said controlled signal.